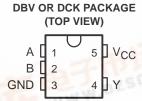
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- EPIC™ (Enhanced-Performance Implanted CMOS) Submicron Process
- I<sub>off</sub> Feature Supports Partial-Power-Down Mode Operation
- Supports 5-V V<sub>CC</sub> Operation
- Package Options Include Plastic Small-Outline Transistor (DBV, DCK) Packages



### description

This single 2-input exclusive - OR gate is designed for 1.65-V to 5.5-V V<sub>CC</sub> operation.

The SN74LVC1G86 performs the Boolean function  $Y = A \oplus B$  or  $Y = \overline{AB} + A\overline{B}$  in positive logic.

A common application is as a true/complement element. If the input is low, the other input is reproduced in true form at the output. If the input is high, the signal on the other input is reproduced inverted at the output.

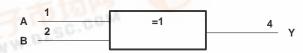
This device is fully specified for partial-power-down applications using I<sub>off</sub>. The I<sub>off</sub> circuitry disables the outputs, preventing damaging current backflow through the device when it is powered down.

The SN74LVC1G86 is characterized for operation from -40°C to 85°C.

### **FUNCTION TABLE**

INP	UTS	OUTPUT
Α	В	Y
L	L	L
L	Н	Н
Н	L	Н
Н	Н	L_ c

### logic symbol†



†This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

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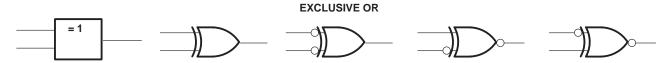
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### SN74LVC1G86 SINGLE 2-INPUT EXCLUSIVE-OR GATE

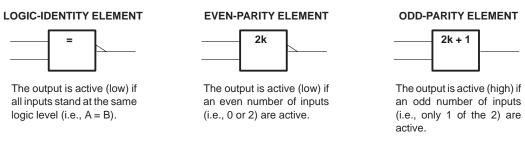
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### exclusive-OR logic

An exclusive-OR gate has many applications, some of which can be represented better by alternative logic symbols.



These are five equivalent exclusive-OR symbols valid for an SN74LVC1G86 gate in positive logic; negation may be shown at any two ports.



### absolute maximum ratings over operating free-air temperature range (unless otherwise noted)

Supply voltage range, V <sub>CC</sub>	
Input voltage range, V <sub>I</sub> (see Note 1)	
Output voltage range, V <sub>O</sub> (see Notes 1 and 2)	
Input clamp current, $I_{IK}$ ( $V_I < 0$ )	
Output clamp current, I <sub>OK</sub> (V <sub>O</sub> < 0)	
Continuous output current, IO	±50 mA
Continuous current through V <sub>CC</sub> or GND	±100 mA
Package thermal impedance, θ <sub>JA</sub> (see Note 3): DBV package	347°C/W
DCK package	389°C/W
Storage temperature range, T <sub>stg</sub>	–65°C to 150°C

<sup>†</sup> Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

- NOTES: 1. The input negative-voltage and output voltage ratings may be exceeded if the input and output current ratings are observed.
  - 2. The value of  $V_{\hbox{\scriptsize CC}}$  is provided in the recommended operating conditions table.
  - 3. The package thermal impedance is calculated in accordance with JESD 51.



### recommended operating conditions (see Note 4)

			MIN	MAX	UNIT	
\/	Cupality voltage	Operating	1.65	5.5	V	
VCC	Supply voltage	Data retention only	1.5		V	
		V <sub>CC</sub> = 1.65 V to 1.95 V	0.65 × V <sub>CC</sub>			
V	High-level input voltage	$V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$	1.7		V	
VIH		$V_{CC} = 3 V \text{ to } 3.6 V$	2		V	
		$V_{CC} = 4.5 \text{ V to } 5.5 \text{ V}$	$0.7 \times V_{CC}$			
		V <sub>CC</sub> = 1.65 V to 1.95 V		0.35 × V <sub>CC</sub>		
\/	Low-level input voltage	$V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$		0.7	V	
VIL	Low-level input voltage	$V_{CC} = 3 V \text{ to } 3.6 V$		0.8	V	
		$V_{CC} = 4.5 \text{ V to } 5.5 \text{ V}$		0.3 × V <sub>CC</sub>		
٧ <sub>I</sub>	Input voltage		0	5.5	V	
٧o	Output voltage		0	VCC	V	
		V <sub>CC</sub> = 1.65 V		-4		
	High-level output current	V <sub>CC</sub> = 2.3 V		-8		
loh		V <sub>CC</sub> = 3 V		-16	mA	
		vCC = 3 v		-24		
		V <sub>CC</sub> = 4.5 V		-32		
		V <sub>CC</sub> = 1.65 V		4		
	Low-level output current	V <sub>CC</sub> = 2.3 V		8		
loL		V 2V		16	mA	
		VCC = 3 V		24		
		V <sub>CC</sub> = 4.5 V		32		
		$V_{CC} = 1.8 \text{ V} \pm 0.15 \text{ V}, 2.5 \text{ V} \pm 0.2 \text{ V}$		20		
$\Delta t/\Delta v$	Input transition rise or fall rate	$V_{CC} = 3.3 \text{ V} \pm 0.3 \text{ V}$		10	ns/V	
		$V_{CC} = 5 V \pm 0.5 V$				
TA	Operating free-air temperature		-40	85	°C	

NOTE 4: All unused inputs of the device must be held at V<sub>CC</sub> or GND to ensure proper device operation. Refer to the TI application report, Implications of Slow or Floating CMOS Inputs, literature number SCBA004.

## SN74LVC1G86 SINGLE 2-INPUT EXCLUSIVE-OR GATE

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## electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER	TEST CONDITIONS	Vcc	MIN	TYP <sup>†</sup>	MAX	UNIT	
	$I_{OH} = -100 \mu\text{A}$	1.65 V to 5.5 V	V <sub>CC</sub> -0.1				
	$I_{OH} = -4 \text{ mA}$	1.65 V	1.2				
\/a++	$I_{OH} = -8 \text{ mA}$	2.3 V	1.7			٧	
VOH	$I_{OH} = -16 \text{ mA}$	3 V	2.4			V	
	$I_{OH} = -24 \text{ mA}$	3 V	2.3				
	$I_{OH} = -32 \text{ mA}$	4.5 V	3.8				
	I <sub>OL</sub> = 100 μA	1.65 V to 5.5 V			0.2		
	I <sub>OL</sub> = 4 mA	1.65 V			0.45	5	
VOL	I <sub>OL</sub> = 8 mA	2.3 V			0.7	٧	
\ VOL	I <sub>OL</sub> = 16 mA	3 V			0.4	J '	
	I <sub>OL</sub> = 24 mA	3 V			0.55		
	I <sub>OL</sub> = 32 mA	4.5 V			0.55		
lį	V <sub>I</sub> = 5.5 V or GND	0 to 5.5 V			±5	μΑ	
l <sub>off</sub>	$V_I$ or $V_O = 5.5 V$	0			±10	μΑ	
Icc	$V_I = V_{CC}$ or GND, $I_O = 0$	1.65 V to 5.5 V			10	μΑ	
∆ICC	One input at V <sub>CC</sub> – 0.6 V, Other inputs at V <sub>CC</sub> or GND	3 V to 5.5 V			500	μΑ	
Ci	$V_I = V_{CC}$ or GND	3.3 V				pF	

<sup>&</sup>lt;sup>†</sup> All typical values are at  $V_{CC}$  = 3.3 V,  $T_A$  = 25°C.

# switching characteristics over recommended operating free-air temperature range (unless otherwise noted) (see Figures 1 through 4)

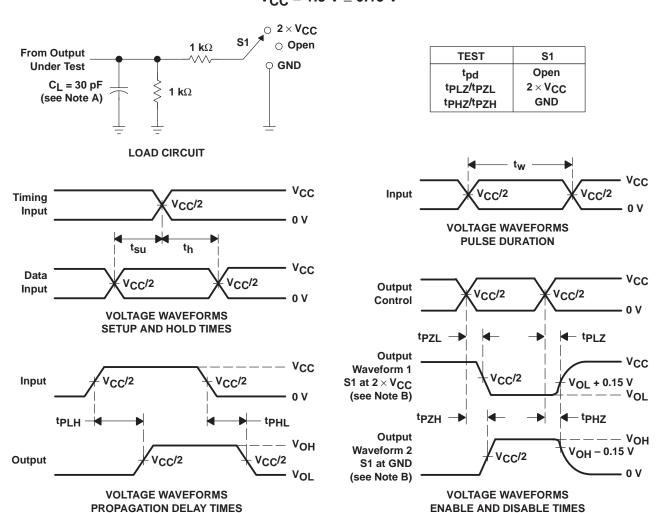
	PARAMETER	FROM (INPUT)	TO (OUTPUT)	V <sub>CC</sub> =		± 0.:		± 0.7		÷ 0.9		UNIT
L		(1141 01)	(0011 01)	MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
	<sup>t</sup> pd	A or B	Y									ns

## operating characteristics, $T_A = 25^{\circ}C$

PARAMETER		DADAMETED	TEST CONDITIONS	V <sub>CC</sub> = 1.8 V	V <sub>CC</sub> = 2.5 V	V <sub>CC</sub> = 3.3 V	V <sub>CC</sub> = 5 V	UNIT
		FARAMETER	TEST CONDITIONS	TYP	TYP	TYP	TYP	ONIT
l	C <sub>pd</sub>	Power dissipation capacitance	f = 10 MHz					pF



# PARAMETER MEASUREMENT INFORMATION $V_{CC} = 1.8 \text{ V} \pm 0.15 \text{ V}$



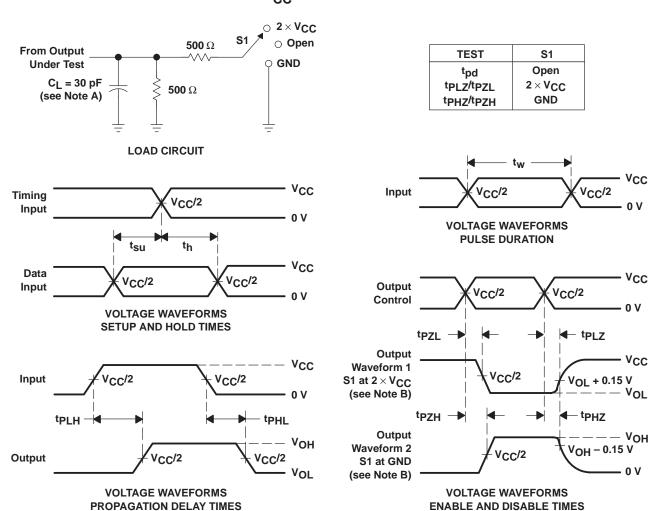
NOTES: A. C<sub>L</sub> includes probe and jig capacitance.

- B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
- C. All input pulses are supplied by generators having the following characteristics: PRR  $\leq$  10 MHz,  $Z_O = 50 \ \Omega$ ,  $t_f \leq$  2 ns.  $t_f \leq$  2 ns.
- D. The outputs are measured one at a time with one transition per measurement.
- E. tpLz and tpHz are the same as tdis.
- F. tpzL and tpzH are the same as ten.
- G. tpLH and tpHL are the same as tpd.

Figure 1. Load Circuit and Voltage Waveforms



# PARAMETER MEASUREMENT INFORMATION $V_{CC} = 2.5 \text{ V} \pm 0.2 \text{ V}$

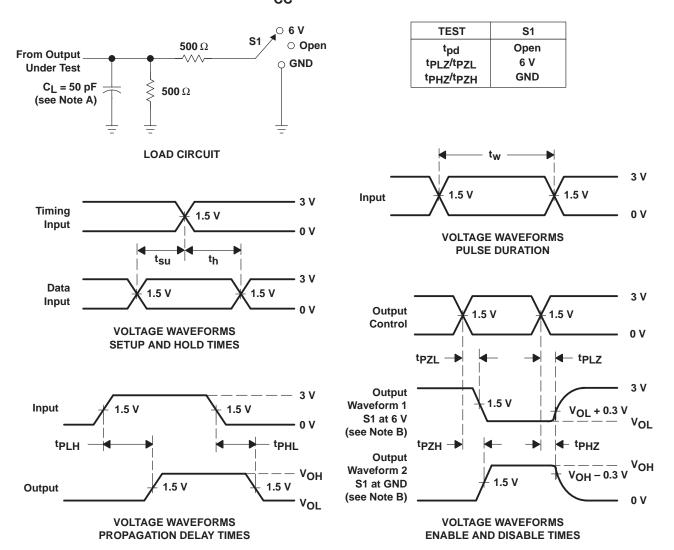


- NOTES: A. C<sub>L</sub> includes probe and jig capacitance.
  - B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
  - C. All input pulses are supplied by generators having the following characteristics: PRR  $\leq$  10 MHz,  $Z_Q$  = 50  $\Omega$ ,  $t_f \leq$  2 ns.  $t_f \leq$  2 ns.
  - D. The outputs are measured one at a time with one transition per measurement.
  - E. tpLz and tpHz are the same as tdis.
  - F. tpzL and tpzH are the same as ten.
  - G. tpLH and tpHL are the same as tpd.

Figure 2. Load Circuit and Voltage Waveforms



# PARAMETER MEASUREMENT INFORMATION $V_{CC} = 3.3 \text{ V} \pm 0.3 \text{ V}$



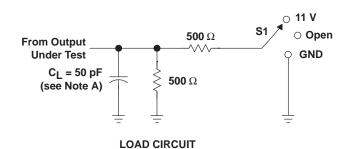
NOTES: A.  $C_L$  includes probe and jig capacitance.

- B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
- C. All input pulses are supplied by generators having the following characteristics: PRR  $\leq$  10 MHz, Z<sub>O</sub> = 50  $\Omega$ ,  $t_f \leq$  2.5 ns,  $t_f \leq$  2.5 ns.
- D. The outputs are measured one at a time with one transition per measurement.
- E.  $t_{PLZ}$  and  $t_{PHZ}$  are the same as  $t_{dis}$ .
- F. tpzL and tpzH are the same as ten.
- G. tplH and tpHL are the same as tpd.

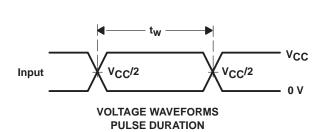
Figure 3. Load Circuit and Voltage Waveforms

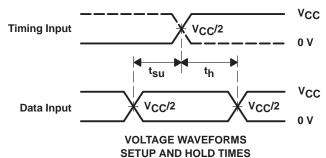


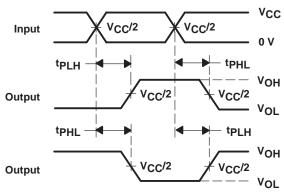
### PARAMETER MEASUREMENT INFORMATION $V_{CC} = 5 V \pm 0.5 V$

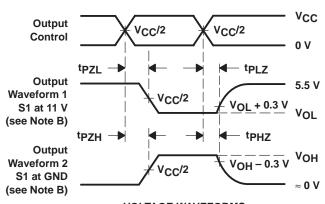


TEST	<b>S</b> 1
tPLH/tPHL tPLZ/tPZL	Open 11 V
<sup>t</sup> PHZ <sup>/t</sup> PZH	GND









**VOLTAGE WAVEFORMS PROPAGATION DELAY TIMES INVERTING AND NONINVERTING OUTPUTS** 

**VOLTAGE WAVEFORMS ENABLE AND DISABLE TIMES** LOW- AND HIGH-LEVEL ENABLING

NOTES: A. C<sub>L</sub> includes probe and jig capacitance.

- B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
- C. All input pulses are supplied by generators having the following characteristics: PRR  $\leq$  10 MHz,  $Z_Q = 50 \Omega$ ,  $t_f \leq 2.5 \text{ ns.}$
- D. The outputs are measured one at a time with one transition per measurement.
- E. tpLz and tpHz are the same as tdis.
- F. tpzL and tpzH are the same as ten.
- G. tpLH and tpHL are the same as tpd.

Figure 4. Load Circuit and Voltage Waveforms



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